



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Lin, et al. Docket No.: TSM02-1369
Serial No.: 10/650,445 Art Unit: 2811
Filed: August 28, 2003 Examiner: TBD
For: Ultra-Thin Body Transistor with Recessed Silicide Contacts

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Respectfully submitted,

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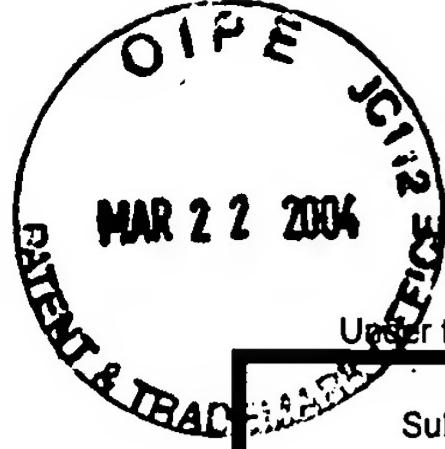
Respectfully submitted,

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March 17, 2004

Date

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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

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	4	Chau, R., et al., "A 50nm Depleted-Substrate CMOS Transistor (DST)," IEDM, pp. 621-624, 2001.	
	5	Choi, Y.K., et al., "Ultrathin-Body SOI MOSFET for Deep-Sub-Tenth Micron Era," IEEE Electron Device Letters, Vol. 21, No. 5, pp. 254-255, May 2000.	
	6	Yeo, Y.C., et al., "Design and Fabrication of 50-nm Thin-Body p-MOSFETs with a SiGe Heterostructure Channel," IEEE Transactions on Electron Devices, Vol. 49, No. 2, pp. 279-286, February 2002.	

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